

ULN2003V12, ULN2003F12 MULTI CHANNEL RELAY AND INDUCTIVE LOAD SINK DRIVER

Description

The ULN2003V12 and ULN2003F12 are multi-channel sink drivers comprised of 7-channel and 4-channel output stages respectively. The ULN2003V12 sink driver features 7 low output impedance drivers that minimize on-chip power dissipation and an actual low power upgrade version for popular ULN2003A family in real applications. When driving a typical 12V relay coil, a ULN2003V12 will dissipate 12 times lower power compared to ULN2003A. ULN2003F12 is a lower power variant benefiting from fewer channel integration and a better fit for applications requiring only 4-channel drivers, such as driving low voltage stepping motors, etc.

The ULN2003V12 and ULN2003F12 both support 3.3V to 5V CMOS logic input interface, thus making it compatible to a wide range of micro-controllers and other logic interfaces, and also feature an improved input interface that minimizes the input DC current drawn from the external drivers. The input RC snubber circuit integrated at ULN2003V12 and ULN2003F12 improves the performance in noisy operating conditions, and the internal pull-down resistor at input stage helps allow input logic to be tri-stated.

As shown in the Functional Diagram, each output of the ULN2003V12 and ULN2003F12 features an internal free-wheeling diode connected in a common-cathode configuration at the COM pin which provides flexibility of increasing current sink capability through combining several adjacent channels in parallel. Under typical conditions the ULN2003V12 can support up to 1.0A of load current when all 7channels are connected in parallel.

Features

- 4- and 7-Channel High Current Sink Drivers
- Supports up to 20V Output Pull-up Voltage
- Low Output VOL of 0.6V (Typical) with
 - 100mA (Typ.) Current Sink per Channel at 3.3V Logic Input
 140mA (Typ.) Current Sink per Channel at 5.0V Logic Input
- Compatible to 3.3V and 5.0V Micro-Controllers and Logic Interface
- Internal Free-Wheeling Diodes for Inductive Kick-back Protection
- Input Pull-down Resistors Allows Tri-Stating the Input Driver
- Input Parton Resistors Anows Throading the input Driver
 Input RC-Snubber to Eliminate Spurious Operation in Noisy Environments
- ESD: 4kV HBM, 1kV CDM
- Available in 16-Pin SOIC, 16-Pin TSSOP and 10-Pin DFN3030 packages
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>





Applications

- Inputs Compatible with Popular Logic Types
- Relay Driver Applications
- Stepping Motor Applications
- Logic Level Shifter

- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
 - 2. See https://www Lead-free
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Functional Diagram



Pin Descriptions

Pin Name Package Number		Description			
Finitianie	SO16	TSSOP16	DFN3030-10	Description	
IN1 ~ IN7	1~7	1~7	1~4	Logic Input Pins IN1 through IN7	
GND	8	8	5	Ground Reference Pin	
СОМ	9	9	6	Internal Free-Wheeling Diode Common Cathode Pin	
OUT7 ~ OUT1	10~16	10~16	7~10	Channel Output Pins OUT7 through OUT1	

Functional Block Diagram (Single Channel)





Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

0. million	Parameter			ting	1114
Symbol				Max	Unit
V _{IN}	Pin2 IN1~IN7 to GND Voltage		-0.3	5.5	V
V _{OUT}	Pins OUT1~OUT7 to GND Voltage			20	V
V _{COM}	Pin COM to GND Voltage			20	V
1	Max GND-Pin Continuous Current (+100°C $$	5°C)	—	700	mA
GND	Max GND-Pin Continuous Current (T _J < +100°C)		_	1.0	А
		16 Pin – SOIC	0.412		W
PD	Total Device Power Dissipation at $T_A = +85^{\circ}C$	16 Pin – TSSOP	0.277		W
		10 Pin – DFN3030	0.615		W
		16 Pin – SOIC	97		
θ_{JA}	Thermal Resistance Junction-to-Ambient (Note 6)	16 Pin – TSSOP	144		°C/W
		10 Pin – DFN3030	65		
		16 Pin – SOIC	41		
θ_{JC}	Thermal Resistance Junction-to-Case (Note 7)	16 Pin – TSSOP	61		°C/W
	10 Pin – DFN3030		17		
HBM				4	kV
ESD	CDM	_	1	kV	
TJ	Junction Temperature	-55	150	°C	
T _{STG}	Storage Temperature			150	°C

Notes: 4. Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied.

Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5. All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.

6. Maximum power dissipation is a function of T_J(max), θ_JA, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is P_D = (T_J(max) – T_A)/θ_JA. Operating at the absolute maximum T_J of +150°C can affect reliability.

7. Maximum power dissipation is a function of TJ(max), θ JC, and TA. The maximum allowable power dissipation at any allowable ambient temperature is PD = (TJ(max) – TC)/ θ JA. Operating at the absolute maximum TJ of +150°C can affect reliability.

Recommended Operating Conditions (@ T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Min	Мах	Unit	
V _{OUT}	Channel Off-Stage Output Pull-Up Voltage	_	_	V	
V _{COM}	COM Pin Voltage	_	—	V	
			_	—	
I _{OUT(ON)} Per Channel Continuous Sink Current		VINx = 5.0V	_	_	mA
TJ	Operating Junction Temperature	-40	_	°C	



Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Specified over the recommended junction temperature range $T_J = -40^{\circ}C$ to $+125^{\circ}C$ and over recommended operating conditions unless otherwise noted. Typical values are at $T_J = +25^{\circ}C$.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units		
INPUTS IN1	NPUTS IN1 THROUGH IN7 PARAMETERS							
V _{I(on)}	IN1~IN7 logic high input voltage	V _{CE} = 2V, I _C = 300mA	1.65		_	V		
V _{I(off)}	IN1~IN7 logic low input voltage	I _I = 250µA, I _C = 100mA	_	_	0.6	V		
I _{I(on)}	IN1~IN7 ON state input current	I _F = 350mA	_	12	25	μA		
I _{I(off)}	IN1~IN7 OFF state input leakage	—	_	—	250	nA		
OUTPUTS O	UT1 THROUGH OUT7 PARAMETERS							
		V _{INX} = 3.3V, I _{OUTX} = 20mA	_	0.12	0.15			
V		V _{INX} = 3.3V, I _{OUTX} = 100mA		0.6	0.75	V		
V OL(vce-sat)		V _{INX} = 5.0V, I _{OUTX} = 20mA		0.09	0.11	v		
		V _{INX} = 5.0V, I _{OUTX} = 140mA		0.6	0.75			
	OUT1~OUT7 ON-state continuous current at	V _{INX} = 3.3V, V _{OUTX} = 0.6V	80	100	_	V		
IOUT(on)	$V_{OUTX} = 0.6V$	V _{INX} = 5.0V, V _{OUTX} = 0.6V	80	140	_	Α		
I _{OUT(on)}	OUT1~OUT7 OFF-state leakage current	$V_{INX} = 0V, V_{OUTX} = V_{COM} = 16V$		0.5	_	μA		
SWITCHING	PARAMETERS							
t _{PHL}	OUT1~OUT7 logic high propagation delay	$V_{INX} = 3.3V, V_{pull-up} = 12V,$ $R_{pull-up} = 1k\Omega$	—	50	70	ns		
t _{PLH}	OUT1~OUT7 logic low propagation delay	$V_{INX} = 3.3V, V_{pull-up} = 12V,$ $R_{pull-up} = 1k\Omega$	_	121	140	ns		
t _{CHANNEL}	Channel-to-channel delay	Over recommended operating conditions and with same test conditions on channels.	_	15	50	ns		
R _{PD}	IN1~IN7 input pull-down resistance	—	210k	300k	390k	Ω		
ζ	IN1~IN7 input filter time constant	—	_	9	_	ns		
C _{OUT}	OUT1~OUT7 output capacitance	V _{INX} = 3.3V, V _{OUTX} = 0.4V		15		pF		
FREE-WHEE	LING DIODE PARAMETERS	-						
VF	Forward voltage drop	I _{F-peak} = 140mA, VF = V _{OUTx} -V _{COM}	—	1.2	—	V		
I _{F-peak}	Diode peak forward current	<u> </u>	—	140	_	mA		



Performance Characteristics



Output Current vs. Input Voltage (One Darlington)

Output Current vs. Input Voltage (All Darlingtons in Parallel)



Output Current vs. Output Voltage



Output Current vs. Output Voltage





Performance Characteristics (continued)



Output Current vs. Output Voltage

Diode Forward Voltage vs. Diode Forward Current



Diode Reverse Current vs. Diode Reverse Voltage





Ordering Information



Dovice	Baakaga Cada	Backaging (Note 9)	7"/13" Tape and Reel		
Device	Package Coue	Fackaging (Note 6)	Quantity	Part Number Suffix	
ULN2003V12S16-13	S16	SO-16	2,500/Tape & Reel	-13	
ULN2003V12T16-13	T16	TSSOP-16	2,500/Tape & Reel	-13	
ULN2003F12FN-7	FN	DFN3030-10	3,000/Tape & Reel	-7	

Note: 8. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

(1) SO-16 and TSSOP-16



(2) DFN3030-10



Part Number	Package	Identification Code
ULN2003F12FN-7	DFN3030-10	A3



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



	SO-16					
Dim	Min	Max	Тур			
Α		1.260				
A1	0.10	0.23				
A2	1.02					
b	0.31	0.51				
С	0.10	0.25				
D	9.80	10.00				
E	5.90	6.10				
E1	3.80	4.00				
е	1	.27 BS	С			
h	0.15	0.25	0.20			
L	0.40	1.27				
L1	1	.04 RE	F			
L2	().25 BS(2			
R	0.07					
R1	0.07	1				
X	3.	.945 RE	F			
Y	0.661 REF					
θ	0°	8°				
θ1	5°	15°				
θ2	0°					
All Dimensions in mm						

E/2 SEE DETAIL 'A' E Ŋ θ1(8**x**) ∠ø0.760Depth0.050±0.02 θ2 A2 R1 12 . D GAUG C SEATING PLANE L A1-۱L1 DETAIL 'A'

	TSSOP-16					
Dim	Min	Max	Тур			
Α	-	1.08	-			
A1	0.05	0.15	-			
A2	0.80	0.93	-			
b	0.19	0.30	-			
С	0.09	0.20	-			
D	4.90	5.10	-			
E	6.40 BSC					
E1	4.30	4.50	-			
е	0).65 BS	С			
L	0.45	0.75	-			
L1	1	.00 RE	F			
L2	0).25 BS	С			
R / R1	0.09	-	-			
Х	-	-	1.350			
Y	-	-	1.050			
θ	0°	8°	-			
θ1	5°	15°	-			
θ2	0°	-	-			
All Di	All Dimensions in mm					

TSSOP-16



Package Outline Dimensions (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.



	U-DFN3030-10						
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.02				
A3			0.15				
b	0.20	0.30	0.25				
D	2.90	3.10	3.00				
D2	2.30	2.50	2.40				
Е	2.90	3.10	3.00				
E2	1.50	1.70	1.60				
е	-		0.50				
L	0.25	0.55	0.40				
z		_	0.375				
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-16



Dimensions	Value (in mm)
С	1.270
X	0.670
X1	9.560
Y	1.450
Y1	6.400

U-DFN3030-10



Suggested Pad Layout (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.



TSSOP-16

Dimonsions	Value
Dimensions	(in mm)
С	0.650
Х	0.350
X1	4.900
Y	1.400
Y1	6.800

U-DFN3030-10



Dimonsions	Value
Dimensions	(in mm)
С	0.50
G	0.15
Х	0.35
X1	2.60
Y	0.60
Y1	1.80

Mechanical Data

- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals:
 - SO-16 and TSSOP-16: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 🕄
 - DFN3030-10: Finish NiPdAu over Copper Lead-Frame, Solderable per MIL-STD-202, Method 208 (3)
- Weight:
 - **SO-16**: 0.129 grams (Approximate)
 - TSSOP-16: 0.055 grams (Approximate)
 - DFN3030-10: 0.016 grams (Approximate)



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